

BT138X series D and E

12 A four-quadrant triacs, sensitive gate Rev. 03 — 10 March 2008

Product data sheet

Product profile

1.1 General description

Passivated sensitive gate triac in a SOT186A full pack plastic package.

1.2 Features

- Very sensitive gate
- Direct interfacing to logic level ICs
- Isolated mounting base
- Gate triggering in four quadrants
- Direct interfacing to low power gate drive circuits
- High isolation voltage

1.3 Applications

General purpose switching and phase control

230 V lamp dimmers

1.4 Quick reference data

- $V_{DRM} \le 600 \text{ V (BT138X-600D)}$
- $V_{DRM} \le 600 \text{ V (BT138X-600E)}$
- $V_{DRM} \le 800 \text{ V (BT138X-800E)}$
- $I_{GT} \le 5 \text{ mA (BT138X-600D)}$
- $I_{GT} \le 10 \text{ mA (BT138X-600E)}$
- $I_{GT} \le 10 \text{ mA (BT138X-800E)}$
- $I_{T(RMS)} \le 12 A$
- $I_{TSM} \le 95 \text{ A (t = 20 ms)}$
- $I_{GT} \le 10 \text{ mA } (T2-G+) \text{ (BT138X-600D)}$
- $I_{GT} \le 25 \text{ mA } (T2-G+) (BT138X-600E)$
- $I_{GT} \le 25 \text{ mA } (T2-G+) \text{ (BT138X-800E)}$



2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	main terminal 1 (T1)		N 1
2	main terminal 2 (T2)	mb	T2—T1
3	gate (G)		`G sym051
mb	mounting base; isolated		
		SOT186A (TO-220F))

3. Ordering information

Table 2. Ordering information

Type number	Package						
	Name	Description	Version				
BT138X-600D	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole;					
BT138X-600E		3-lead TO-220 'full pack'					
BT138X-800E							

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

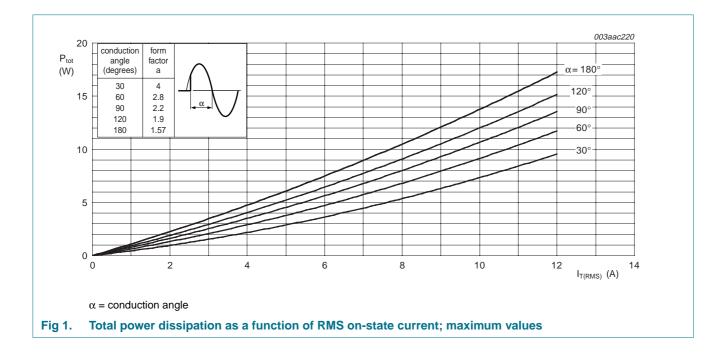
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage	BT138X-600D	<u>[1]</u> _	600	V
		BT138X-600E	<u>[1]</u> _	600	V
		BT138X-800E	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 56$ °C; see Figure 4 and 5	-	12	Α
I _{TSM} non-repetitive	non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3			
		t = 20 ms	-	95	Α
		t = 16.7 ms	-	105	Α
I ² t	I ² t for fusing	t _p = 10 ms	-	45	A^2s
dI _T /dt	rate of rise of on-state current	$I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$			
		T2+ G+	-	50	A/μs
		T2+ G-	-	50	A/μs
		T2- G-	-	50	A/μs
		T2- G+	-	10	A/μs
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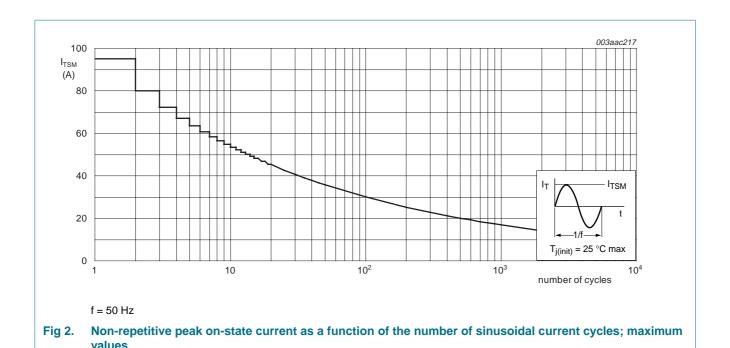
 Table 3.
 Limiting values ...continued

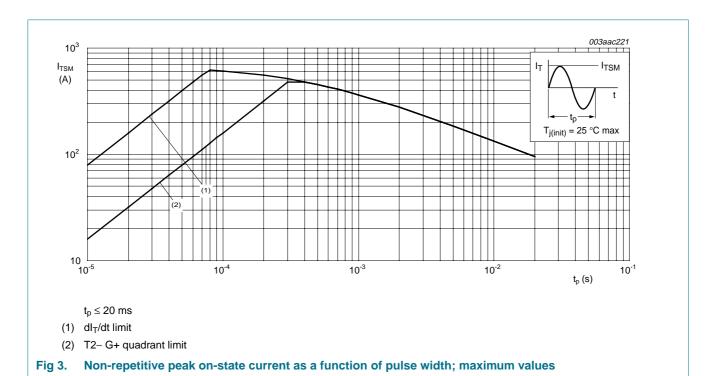
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I_{GM}	peak gate current		-	2	Α
P_GM	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	125	°C

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/μs.







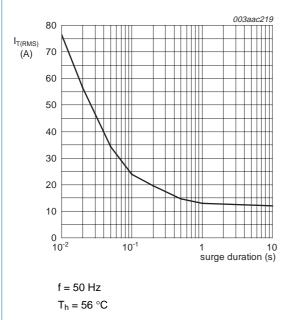


Fig 4. RMS on-state current as a function of surge duration; maximum values

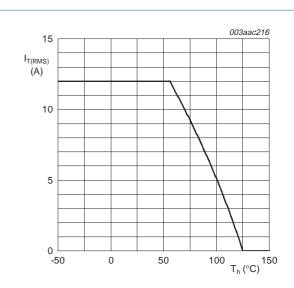
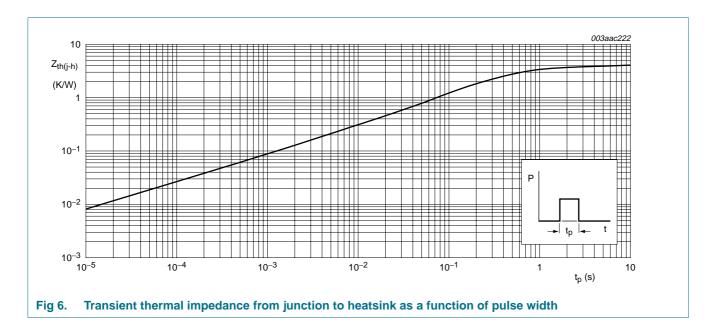


Fig 5. RMS on-state current as a function of heatsink temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle; see Figure 6	-	-	4.0	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	full cycle; in free air	-	55	-	K/W



6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all three terminals to external heatsink; $f = 50 \text{ Hz}$ to 60 Hz ; sinusoidal waveform; relative humidity $\leq 65 \text{ \%}$; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from pin 2 to external heatsink; f = 1 MHz	-	10	-	pF

7. Static characteristics

Table 6. Static characteristics

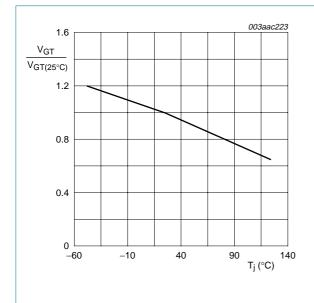
 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions		BT138X-600D		BT13 BT13	Unit		
			Min	Тур	Max	Min	Тур	Max	
I_{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ see } \frac{\text{Figure 8}}{}$	•	'			·	'	
		T2+ G+	-	1.3	5	-	2.5	10	mA
		T2+ G-	-	2.8	5	-	4.0	10	mA
		T2- G-	-	3.2	5	-	5.0	10	mA
		T2- G+	-	5.5	10	-	11	25	mA
I _L latching current		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 10}{\text{Figure } 10}$							
		T2+ G+	-	-	15	-	-	30	mA
		T2+ G-	-	-	20	-	-	40	mA
		T2- G-	-	-	15	-	-	30	mA
		T2- G+	-	-	20	-	-	40	mA
I _H	holding current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 11}{\text{Figure } 11}$	-	-	10	-	-	30	mA
V_{T}	on-state voltage	I _T = 15 A; see <u>Figure 9</u>	-	1.4	1.65	-	1.4	1.65	V
V_{GT}	gate trigger voltage	$I_T = 0.1 \text{ A; see } \underline{\text{Figure 7}}$							
		V _D = 12 V	-	0.7	1.5	-	0.7	1.5	V
		$V_D = V_{DRM}$; $T_j = 125 ^{\circ}C$	0.25	0.4	-	0.25	0.4	-	V
I_D	off-state current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-	0.1	0.5	-	0.1	0.5	mA

8. Dynamic characteristics

Table 7. Dynamic characteristics

Symbol	Parameter	Conditions	BT138X-600D			BT138X-600E BT138X-800E			Unit
			Min	Тур	Max	Min	Тур	Max	
dV _D /dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)};$ exponential waveform; gate open circuit; $T_j = 125 ^{\circ}C$	-	50	-	-	150	-	V/μs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 16 \text{ A};$ $V_D = V_{DRM(max)};$ $I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	-	2	-	μs

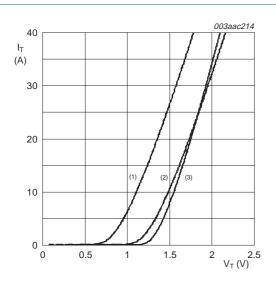


- (1) T2-G+
- (2) T2-G-
- (3) T2+ G-
- (4) T2+ G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature

BT138X_SER_D_E_3



 $V_0 = 1.175 \text{ V}$

 $R_s = 0.032 \Omega$

(1) $T_j = 125 \,^{\circ}C$; typical values

(2) T_i = 125 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig 9. On-state current as a function of on-state voltage

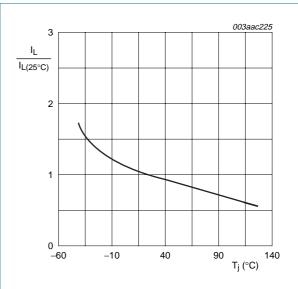


Fig 10. Normalized latching current as a function of junction temperature

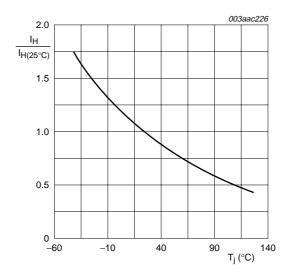
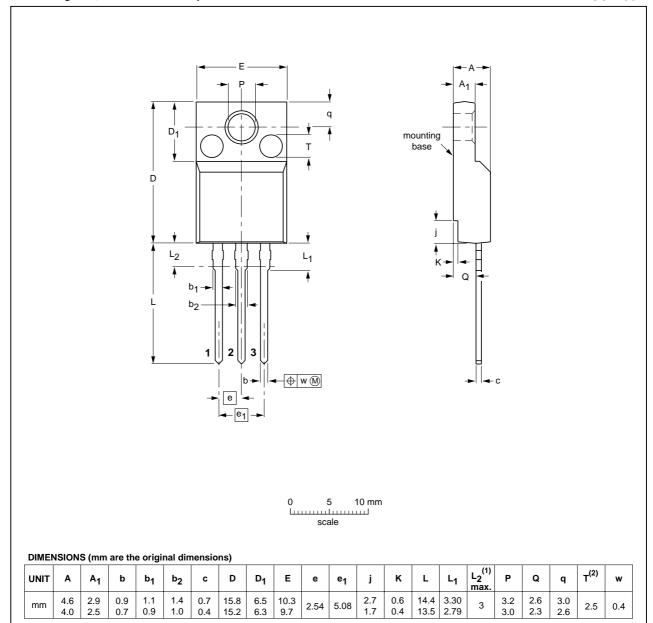


Fig 11. Normalized holding current as a function of junction temperature

9. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT186A		3-lead TO-220F				02-04-09 06-02-14

Fig 12. Package outline SOT186A (TO-220F)

BT138X series D and E

12 A four-quadrant triacs, sensitive gate

10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
BT138X_SER_D_E_3	20080310	Product data sheet	-	BT138X_SERIES_E_2				
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 							
	 Legal texts have been adapted to the new company name where appropriate. 							
	 BT138X-600 	OD product added.						
	• Table 7 "Dyi	namic characteristics": dV _D /	dt uprated for BT138X s	series E.				
BT138X_SERIES_E_2	20010601	Product data sheet	-	BT138X_SERIES_E_1				
BT138X_SERIES_E_1	19970901	Product data sheet	-	-				

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11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors

BT138X series D and E

12 A four-quadrant triacs, sensitive gate

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